



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

M. IZAWA et al

Serial No. 09/373,723

Group Art Unit: 1763

Filed: August 13, 1999

Examiner: ALEJANDRO, L.

For: A DRY ETCHING METHOD

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated October 2, 2001, please amend the above-identified application as follows.

A Petition and fee for a two-month Extension of Time also accompany this response.

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IN THE SPECIFICATION

Page 1, the first full paragraph, lines 5-9, replace the paragraph as follows:

The present invention relates to a dry etching method used for fine manufacturing of semiconductor devices, particularly, to a dry etching method for realizing high-precision dry etching manufacturing of silicone oxide film.

Page 14, the fourth full paragraph, lines 16-19, replace the paragraph as follows: